

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMEX.256	APPLICATION NO. 09/452,844
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Raaijmakers et al.	
		FILING DATE December 3, 1999	GROUP 2811

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
RNR		4,058,430	11/15/77	Suntola et al.	156	611	
RNR		4,747,367	5/31/88	Posa	118	715	
RNR		4,761,269	8/2/88	Conger et al.	422	245	
RNR		5,071,670	12/10/91	Kelly	427	38	
RNR		5,418,180	5/23/95	Brown	437	60	
RNR		5,608,247	3/97	Brown	257	306	
RNR		5,688,724	11/18/97	Yoon et al.	437	235	
RNR		5,769,950	6/23/98	Takasu et al.	118	715	
RNR		5,916,365	6/29/99	Sherman	117	92	

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
RNR	Abeles, et al., "Amorphous Semiconductor Superlattices," Physical Review Letters, Vol. 51, No. 21, Nov. 21, 1983, pg. 2003 - 2006.
RNR	Adler et al., "Single-Device Memory Cell Having A Transistor Metal Silicate Capacitor Dielectric And Ion-Implanted Storage Node," IBM Technical Disclosure Bulletin, Vol. 25, No. 7A, Dec. 1982, pg. 3494 - 3495.
RNR	Desu, et al., "Enhanced dielectric properties of modified Ta2O5 thin films," Mat. Res. Innovat., Vol. 2, 1999, pg 299 - 302.
RNR	Fazan et al., "A High-C Capacitor (20.4 fF/ μm^2) with Ultrathin CVD - Ta2O5 Films Deposited on Rugged Poly-Si for High Density DRAMs," IEDM, 1992, pg. 263 - 266.
RNR	Kim et al., "The effects of substrate and annealing ambient on the electrical properties of Ta2O5 thin films prepared by plasma enhanced chemical vapor deposition," Thin Solid Films, Vol. 253, 1994, pg. 435 - 439.
RNR	Kim et al., "Novel poly-Si/Al2O3/poly-Si Capacitor for High Density DRAMs," 1998 Symposium on VLSI Technology Digest of Technical Papers, pg. 52 - 53
RNR	Kukli et al., "Atomic Layer Epitaxy Growth of Tantalum Oxide Thin Films from Ta(OC2H5)5 and H2O," J. Electrochem. Soc., Vol. 142, No. 5, May 1995, pg. 1670 - 1674.
RNR	Leskelä, et al., "Atomic Layer Epitaxy in Deposition of Various Oxide and Nitride Thin Films," Journal De Physique IV, Vol. 5, June 1995, pg. C5-937 - C5-951.
RNR	Niinistö, et al., "Synthesis of oxide thin films and overlayers by atomic layer epitaxy for advanced applications," Materials Science and Engineering B41, 1996, pg. 23 - 29.
RNR	Ritala, et al., "Perfectly Conformal TiN and Al2O3 Films Deposited by Atomic Layer Deposition," Chemical Vapor Deposition, Vol. 5, No. 1, 1999, pg. 7 - 9.
RNR	Ritala, et al., "Zirconium dioxide thin films deposited by ALE using zirconium tetrachloride as precursor," Applied Surface Science, Vol. 75, 1994, pg. 333 - 340.
RNR	Sakaue, et al., "Digital Chemical Vapor Deposition of SiO2 Using a Repetitive Reaction of Triethylsilane/Hydrogen and Oxidation," Japanese Journal of Applied Physics, Vol. 30, No. 1B, Jan. 1990, pg. L124 - L127.
RNR	Singer, Peter, "Wafer Processing: Atomic Layer Deposition Targets Thin Films," Semiconductor International, Vol. 22, No. 10, Sept. 1999, pg. 40.
RNR	Sneh, et al., "Atomic layer growth of SiO2 on Si(100) using SiCl4 and H2O in a binary reaction sequence," Surface Science, Vol. 334, 1995, pg. 135 - 152.

EXAMINER	Ruero Roach:ami	DATE CONSIDERED	3/21/01
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EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
PWR	Tiitta, et al., "Preparation and Characterization of Phosphorus-Doped Aluminum Oxide Thin Films," Materials Research Bulletin, Vol. 33, No. 9, 1998, pg. 1315 - 1323.
PWR	Vehkamäki, et al., "Growth of SrTiO ₃ and BaTiO ₃ Thin Films by Atomic Layer Deposition," Electrochemical and Solid-State Letters, Vol. 2, No. 10, 1999, pg. 504 - 506.
PWR	Wise, et al., "Diethyldiethoxysilane As A New Precursor For SiO ₂ Growth On Silicon," Mat. Res. Soc. Symp. Proc., Vol. 334, 1994, pg. 37 - 43.

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EXAMINER <i>Renzo Rocheigiani</i>	DATE CONSIDERED <i>3/21/01</i>
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